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Kind regards,

Team Nexperia



# PBSS3540MB

40 V, 0.5 A PNP low  $V_{CEsat}$  (BISS) transistor

Rev. 1 — 7 March 2012

Product data sheet

## 1. Product profile

### 1.1 General description

PNP low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor in a leadless ultra small SOT883B Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS2540MB.

### 1.2 Features and benefits

- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm
- Low collector-emitter saturation voltage  $V_{CEsat}$
- High collector current capability  $I_C$  and  $I_{CM}$
- High efficiency due to less heat generation
- AEC-Q101 qualified
- Reduced Printed-Circuit Board (PCB) requirements

### 1.3 Applications

- DC-to-DC conversion
- Supply line switching
- Battery charger
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)

### 1.4 Quick reference data

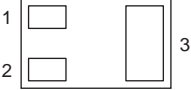
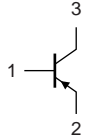
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-40	V
$I_C$	collector current		-	-	-500	mA
$I_{CM}$	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	-1	A
$R_{CEsat}$	collector-emitter saturation resistance	$I_C = -500$ mA; $I_B = -50$ mA; pulsed; $t_p \leq 300$ $\mu$ s; $\delta \leq 0.02$ ; $T_{amb} = 25$ °C	-	440	700	m $\Omega$



## 2. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	B	base	 <p>Transparent top view</p> <p><b>SOT883B</b></p>	 <p>sym013</p>
2	E	emitter		
3	C	collector		

## 3. Ordering information

**Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
PBSS3540MB	-	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B

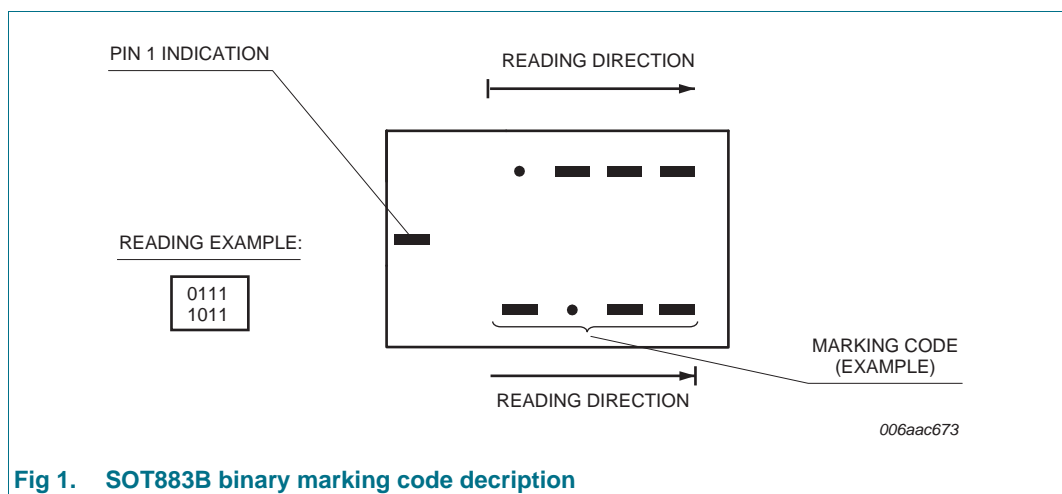
## 4. Marking

**Table 4. Marking codes**

Type number	Marking code <sup>[1]</sup>
PBSS3540MB	0001 0100

[1] For SOT883B binary marking code description see [Figure 1](#).

### 4.1 Binary marking code description



## 5. Limiting values

**Table 5. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter	-	-40	V
$V_{CEO}$	collector-emitter voltage	open base	-	-40	V
$V_{EBO}$	emitter-base voltage	open collector	-	-6	V
$I_C$	collector current		-	-500	mA
$I_{CM}$	peak collector current	single pulse; $t_p \leq 1$ ms	-	-1	A
$I_{BM}$	peak base current	single pulse; $t_p \leq 1$ ms	-	-100	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25$ °C	<a href="#">[1][2]</a>	250	mW
			<a href="#">[3][2]</a>	590	mW
$T_j$	junction temperature		-	150	°C
$T_{amb}$	ambient temperature		-55	150	°C
$T_{stg}$	storage temperature		-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

## 6. Thermal characteristics

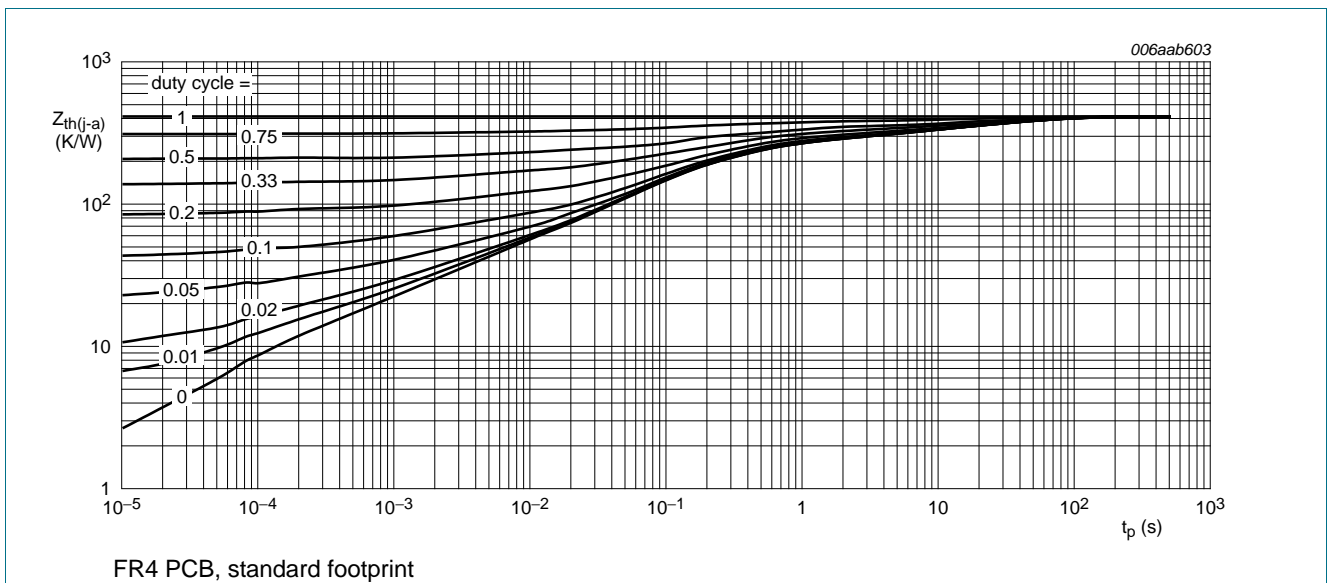
**Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1][2]	-	-	500	K/W
			[3][2]	-	-	212	K/W

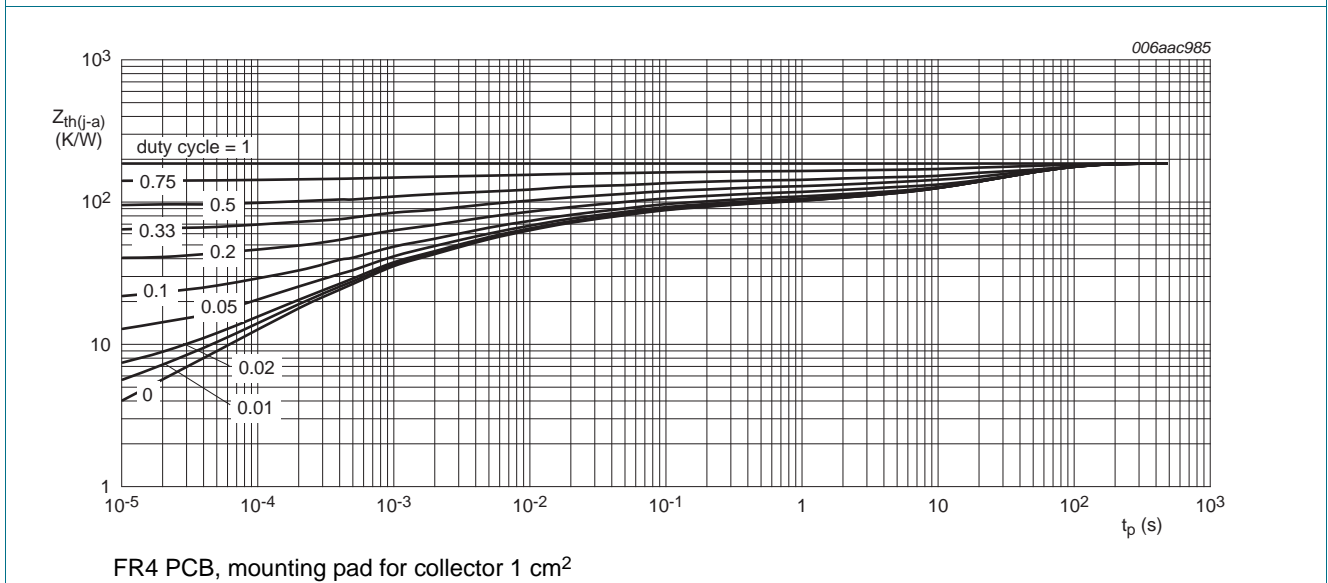
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.



**Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values**

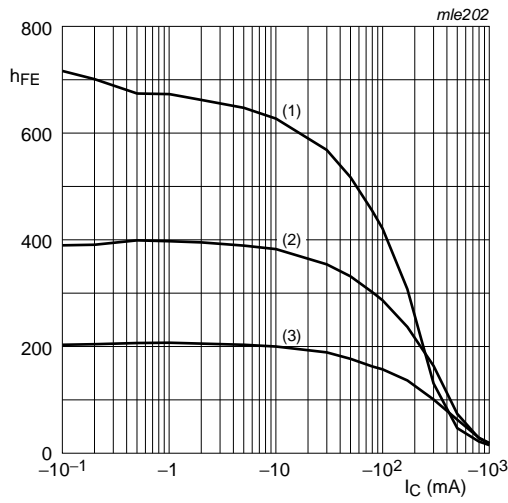


**Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values**

## 7. Characteristics

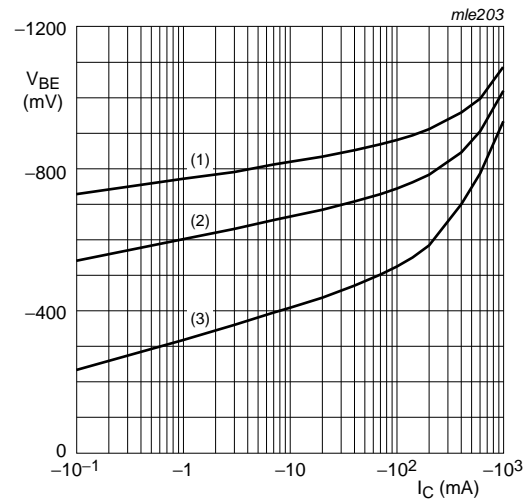
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{CBO}$	collector-base cut-off current	$V_{CB} = -30\text{ V}; I_E = 0\text{ A}; T_{amb} = 25\text{ }^\circ\text{C}$	-	-	-100	nA
		$V_{CB} = -30\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^\circ\text{C}$	-	-	-50	$\mu\text{A}$
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = -5\text{ V}; I_C = 0\text{ A}; T_{amb} = 25\text{ }^\circ\text{C}$	-	-	-100	nA
$h_{FE}$	DC current gain	$V_{CE} = -2\text{ V}; I_C = -10\text{ mA}; T_{amb} = 25\text{ }^\circ\text{C}$	200	-	-	
		$V_{CE} = -2\text{ V}; I_C = -100\text{ mA};$ pulsed; $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^\circ\text{C}$	150	-	-	
		$V_{CE} = -2\text{ V}; I_C = -500\text{ mA};$ pulsed; $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^\circ\text{C}$	40	-	-	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA}; T_{amb} = 25\text{ }^\circ\text{C}$	-	-	-50	mV
		$I_C = -100\text{ mA}; I_B = -5\text{ mA};$ pulsed; $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^\circ\text{C}$	-	-	-130	mV
		$I_C = -200\text{ mA}; I_B = -10\text{ mA};$ pulsed; $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^\circ\text{C}$	-	-	-200	mV
		$I_C = -500\text{ mA}; I_B = -50\text{ mA};$ pulsed; $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^\circ\text{C}$	-	-	-350	mV
$R_{CEsat}$	collector-emitter saturation resistance	$I_C = -500\text{ mA}; I_B = -50\text{ mA};$ pulsed; $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^\circ\text{C}$	-	440	700	m $\Omega$
$V_{BEsat}$	base-emitter saturation voltage	$I_C = -500\text{ mA}; I_B = -50\text{ mA};$ pulsed; $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^\circ\text{C}$	-	-	-1.2	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = -2\text{ V}; I_C = -100\text{ mA};$ pulsed; $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^\circ\text{C}$	-	-	-1.1	V
$f_T$	transition frequency	$V_{CE} = -5\text{ V}; I_C = -100\text{ mA}; f = 100\text{ MHz};$ $T_{amb} = 25\text{ }^\circ\text{C}$	100	300	-	MHz
$C_c$	collector capacitance	$V_{CB} = -10\text{ V}; I_E = 0\text{ A}; i_e = 0\text{ A};$ $f = 1\text{ MHz}; T_{amb} = 25\text{ }^\circ\text{C}$	-	-	10	pF



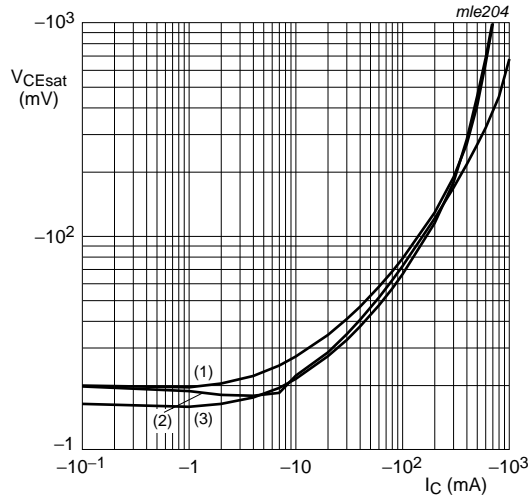
$V_{CE} = -2\text{ V}$   
 (1)  $T_{amb} = 150\text{ }^{\circ}\text{C}$   
 (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$   
 (3)  $T_{amb} = -55\text{ }^{\circ}\text{C}$

**Fig 4. DC current gain as a function of collector current; typical values**



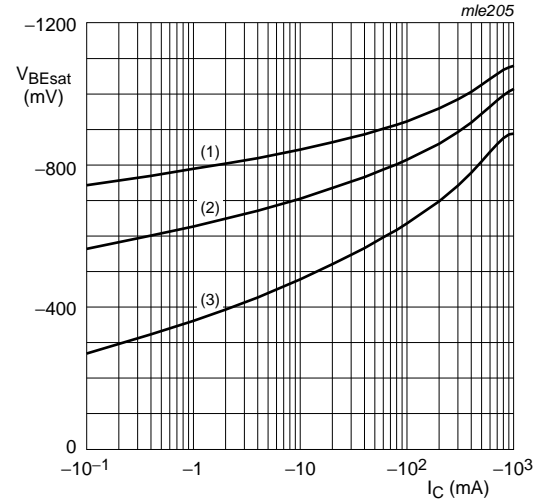
$V_{CE} = -2\text{ V}$   
 (1)  $T_{amb} = -55\text{ }^{\circ}\text{C}$   
 (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$   
 (3)  $T_{amb} = 150\text{ }^{\circ}\text{C}$

**Fig 5. Base-emitter voltage as a function of collector current; typical values**



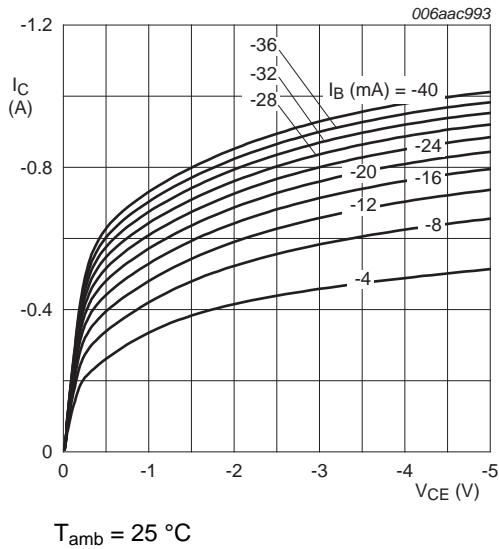
$I_C/I_B = 20$   
 (1)  $T_{amb} = 150\text{ }^{\circ}\text{C}$   
 (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$   
 (3)  $T_{amb} = -55\text{ }^{\circ}\text{C}$

**Fig 6. Collector-emitter saturation voltage as a function of collector current; typical values**

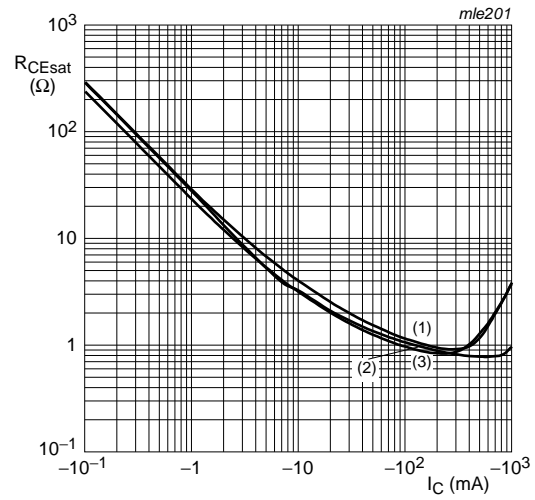


$I_C/I_B = 20$   
 (1)  $T_{amb} = 150\text{ }^{\circ}\text{C}$   
 (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$   
 (3)  $T_{amb} = -55\text{ }^{\circ}\text{C}$

**Fig 7. Base-emitter saturation voltage as a function of collector current; typical values**



**Fig 8. Collector current as a function of collector-emitter voltage; typical values**



$I_C/I_B = 20$   
 (1)  $T_{amb} = 150\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = -55\text{ }^\circ\text{C}$

**Fig 9. Collector-emitter equivalent on-resistance as a function of collector current; typical values**

## 8. Test information

### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.





## 11. Revision history

**Table 8. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS3540MB v.1	20120307	Product data sheet	-	-

## 12. Legal information

### 12.1 Data sheet status

Document status <sup>[1] [2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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